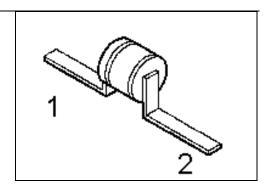


HiRel Silicon Schottky Diode

- HiRel Discrete and Microwave Semiconductor
- General-purpose diodes for high-speed switching
- Circuit protection
- Voltage clamping
- High-level detecting and mixing
- Hermetically sealed microwave package
- Cesa Space Qualified

ESA/SCC Detail Spec. No.: 5512/020

Type Variant No. 03



ESD: Electrostatic discharge sensitive device, observe handling precautions!

Туре	Marking	Ordering Code	Pin Configuration	Package
BAS40-T1 (ql)	-	see below	1 — 2	T1

(ql) Quality Level: P: Professional Quality

H: High Rel QualityS: Space Quality

ES: ESA Space Quality

(see order instructions for ordering example)



Maximum Ratings

Parameter	Symbol	Values	Unit
Reverse Voltage	V _R	40	V
Forward Current	I _F	120	mA
Surge Forward Current 1)	I _{FSM}	170	mA
Power Dissipation 2)	P _{tot}	250	mW
Operating Temperature Range	T _{op}	-55 to +150	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Soldering Temperature 3)	T _{sol}	+250	°C
Junction Temperature	Tj	150	°C
Thermal Resistance Junction-Case	R _{th(j-c)}	100	K/W

Electrical Characteristics

at T_A=25°C; unless otherwise specified

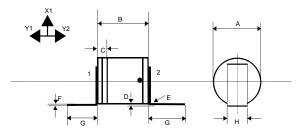
Parameter	Symbol	Values Unit			
		min.	typ.	max.	
DC Characteristics					
Reverse Current 1, V _R =40V	I _{R1}	-	-	10	μΑ
Reverse Current 2, V _R =30V	I _{R2}	-	-	1	μΑ
Forward Voltage 1, I _{F1} =1mA	V _{F1}	0,29	0,33	0,39	V
Forward Voltage 2, I _{F2} =10mA	V_{F2}	0,42	0,45	0,54	V
Forward Voltage 3, I _{F3} =40mA	V_{F3}	0,68	0,7	0,85	V
Differential Forward Resistance 4)	R _{FD}	7,5	10	11,5	Ω
IF=10mA, IF=15mA					
AC Characteristics					
Total Capacitance	Ст	2,2	2,9	5,0	pF
V _R =0V; f=1MHz					

Notes.:

- $\overline{1.)}$ t \leq 10ms, Duty Cycle=10%
- 2.) At T_{CASE} = 125 °C. For T_{CASE} > 125 °C derating is required.
 3.) During 5 sec. maximum. The same terminal shall not be resoldered until 3 minutes have elapsed.



T1 Package



Symbol	Millimetre		
	min	max	
Α	1,30	1,45	
В	1,15	1,35	
С	-	0,40	
D	0,10	0,50	
Е	-	0,30	
F	0,06	0,10	
G	5,50	-	
Н	0,40	0,60	

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